

奈良先端科学技術大学院大学物質創成科学研究科  
量子物性科学講座 柳 久雄

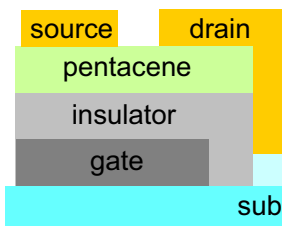
「ソフトマテリアルを用いた新しい有機発光デバイス」

1. 研究室紹介と研究背景
2. 有機発光トランジスタ
3. 有機発光増幅器と有機ラマンレーザー
4. CNT複合体を用いたフィールドエミッションデバイス

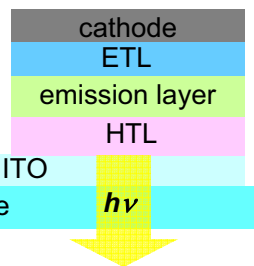


有機発光トランジスタ (OLET)

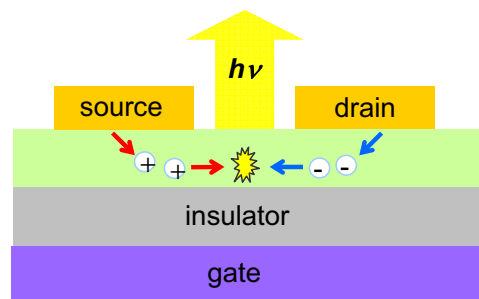
有機電界効果型トランジスタ (OFET)



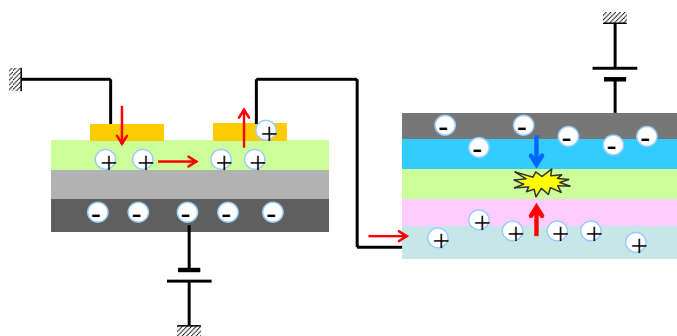
有機EL (OEL)



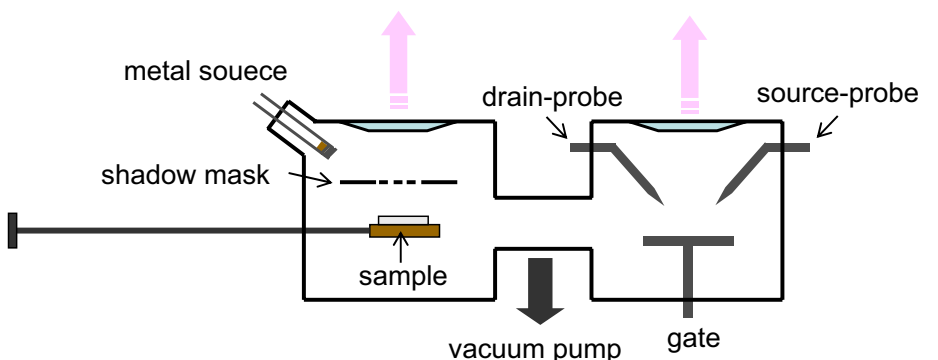
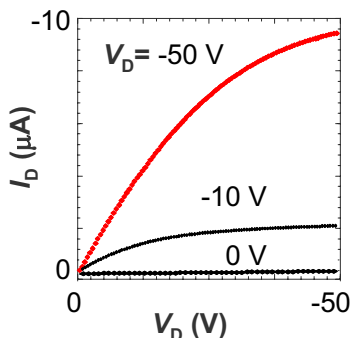
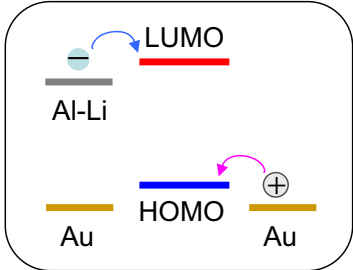
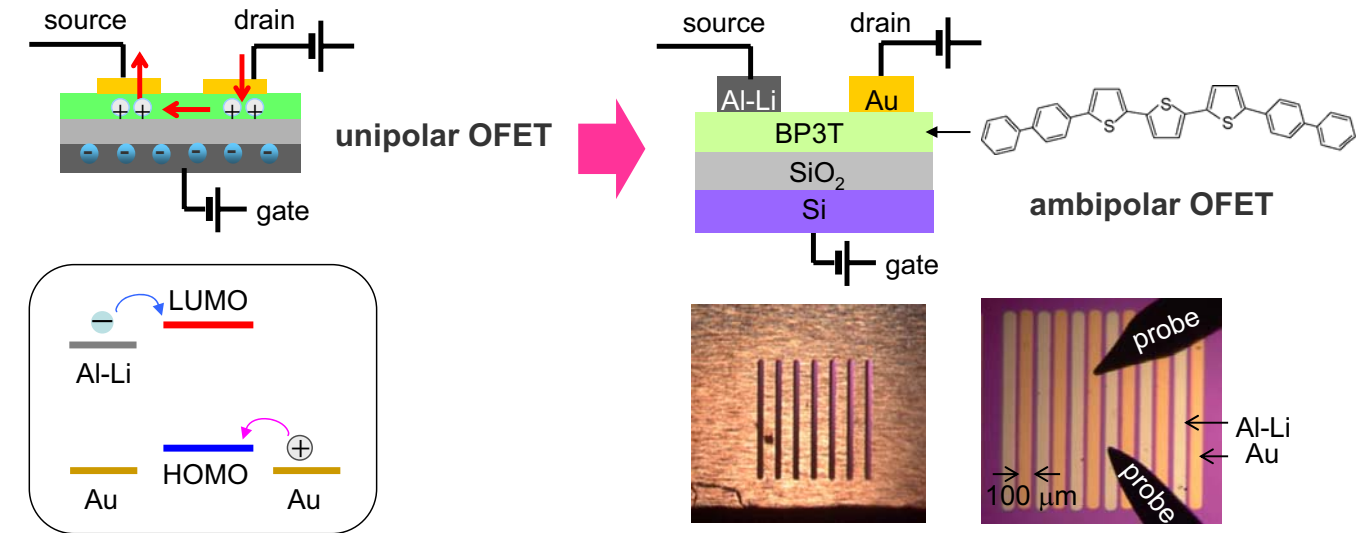
有機発光トランジスタ (OLET)  
Organic Light-Emitting Transistor (OLET)



構造がシンプル  
低コストプロセス  
高電流注入が可能



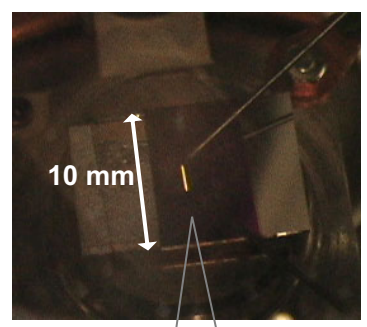
# Ambipolar OLETの作製



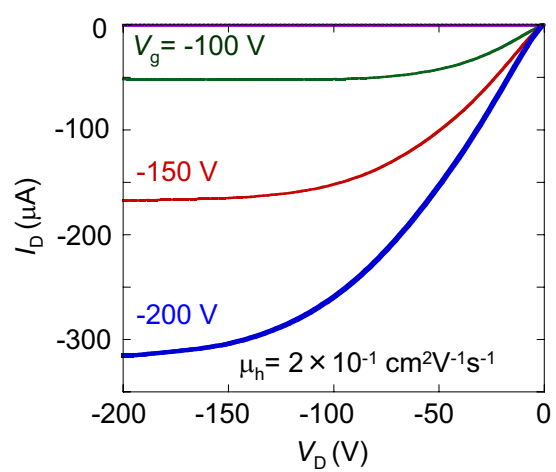
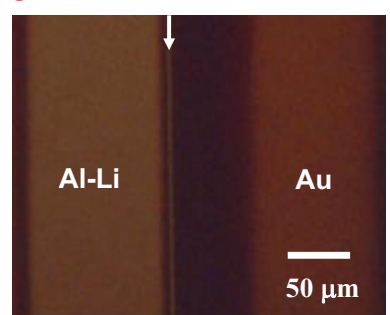
[K. Yamane, H. Yanagi, A. Sawamoto and S. Hotta, *Appl. Phys.* **45**, L650 (2006)]

# OLETの電流-電圧、発光の特性

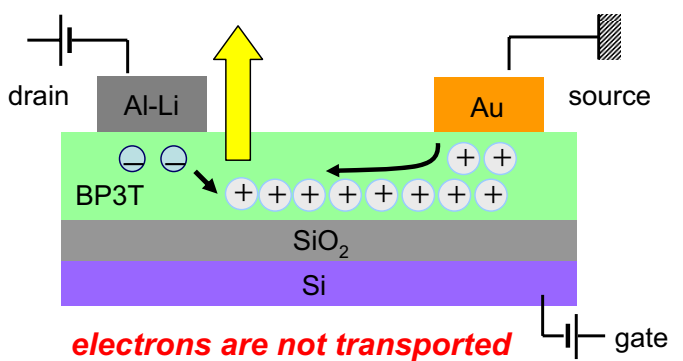
$V_G < -100 \text{ V}, V_D < -100 \text{ V}$



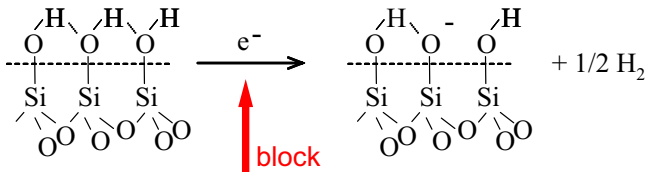
light-emission at Al-Li drain



p-type unipolar I-V curve

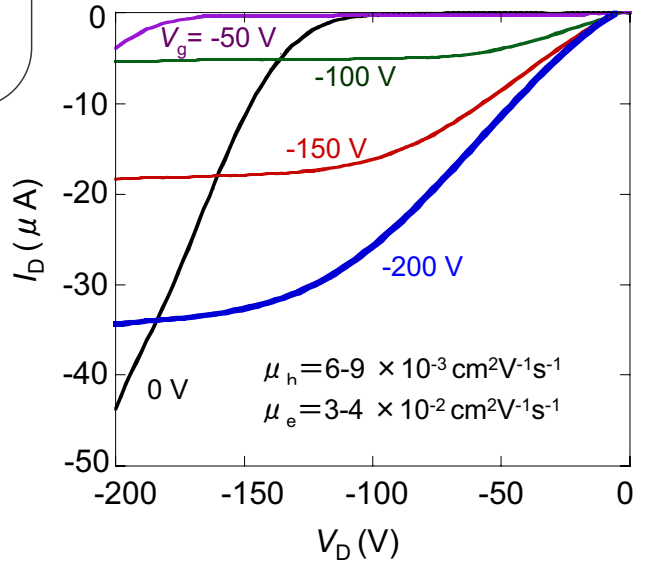
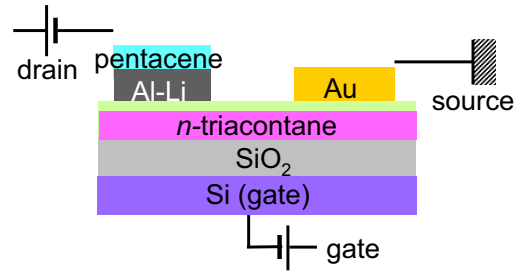
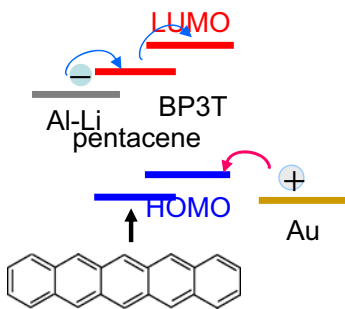


## SiO<sub>2</sub> defect with O-H groups traps electrons



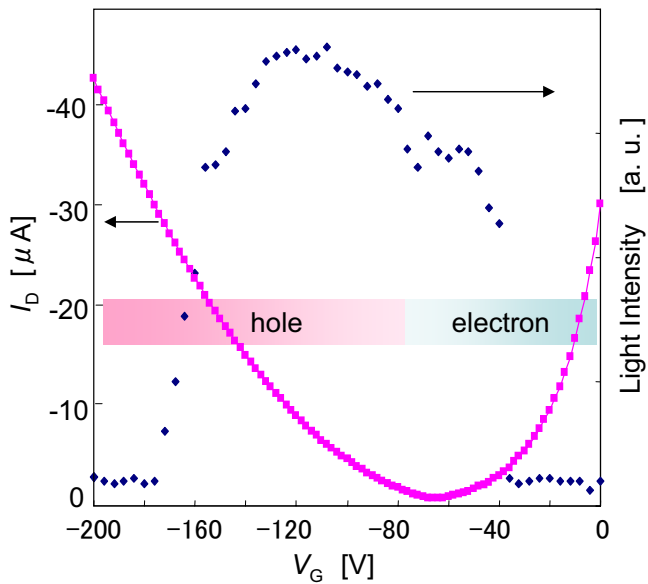
*n*-triacontane (C<sub>30</sub>H<sub>62</sub>) layer

## electron injection layer of pentacene

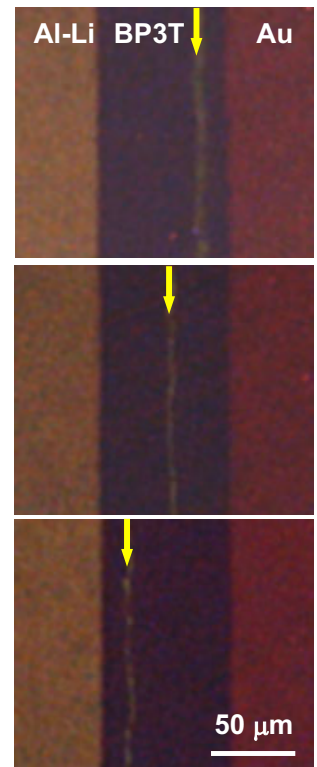
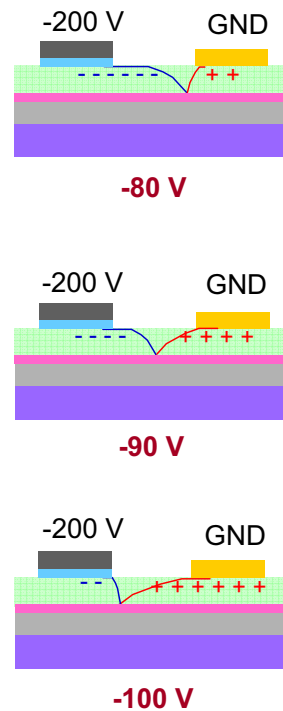


**ambipolar carrier transport**

# Ambipolar OFETのゲート電圧による発光制御

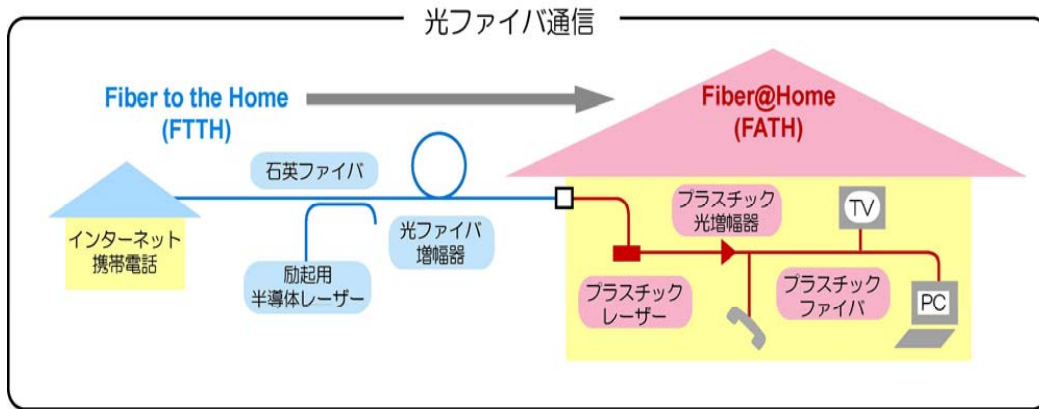


Dependence of  $I_D$  and light intensity on  $V_G$

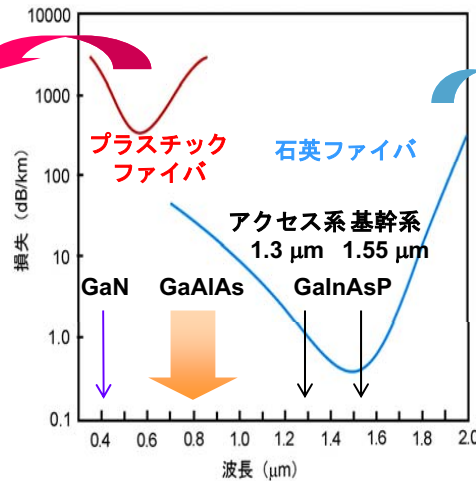


再結合発光位置を  $V_G$  により制御できる → 電極による消光を抑制  
 高密度のキャリアと発光を狭い一次元領域に閉じ込められる

**有機レーザー ダイオード(OLD)**

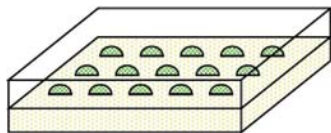


- ◆ 有機半導体レーザー (OSL)  
可視-近赤外光帯域  
(0.5~0.8 μm)
- ◆ 有機光増幅器 (OOA)  
小型・集積化・フレキシブル

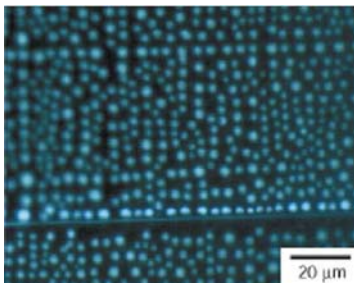


- ◆ 光ファイバ増幅器
- ・Erドープ光ファイバ増幅器  
高利得(~30dB), 低雑音  
ファイバ長: 5~50m
- ・光ファイバラマン増幅器(FRA)  
誘導ラマン散乱(SRS)現象  
任意の波長で利得  
ファイバ長: 数km

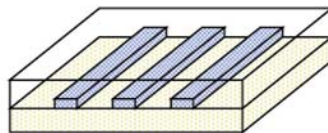
0-Dimension



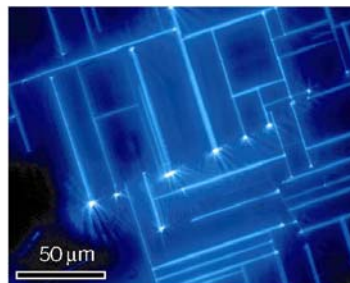
Molecular Dot



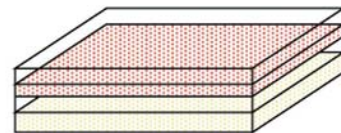
1-Dimension



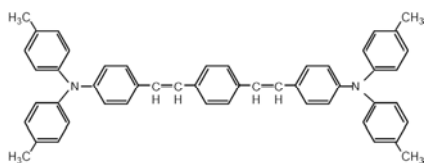
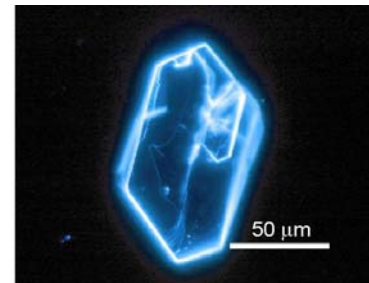
Molecular Needle



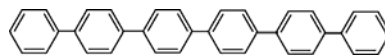
2-Dimension



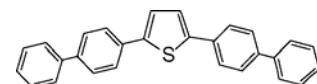
Molecular Layer



bis-styrylbenzene (BSB)



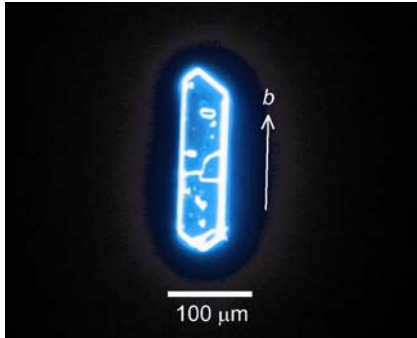
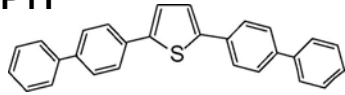
p-sexipheny (p-6P)



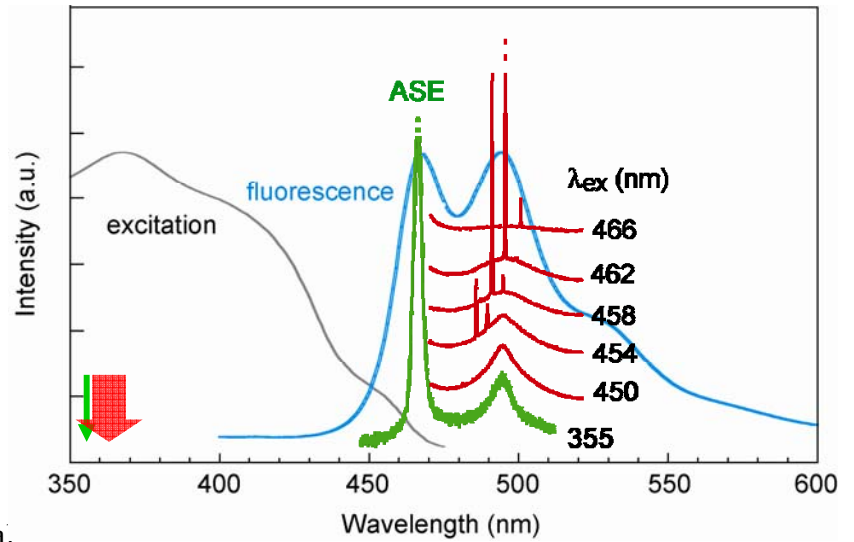
bis-biphenyl thiophene (BP1T)



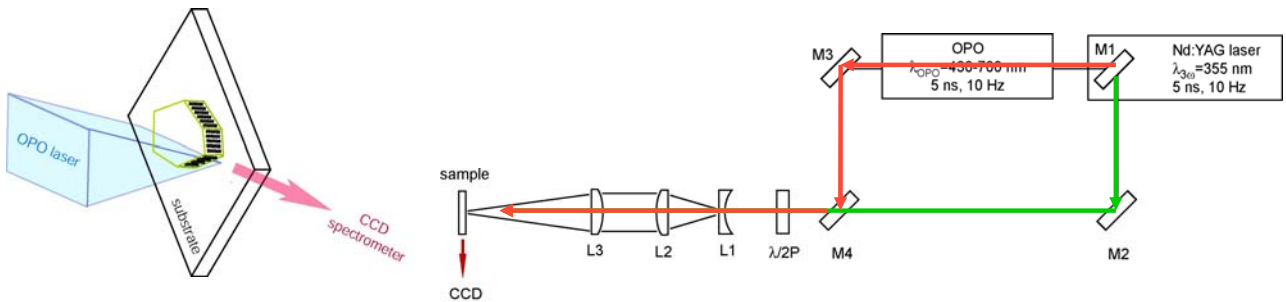
BP1T



Fluorescence micrograph of BP1T crystal.

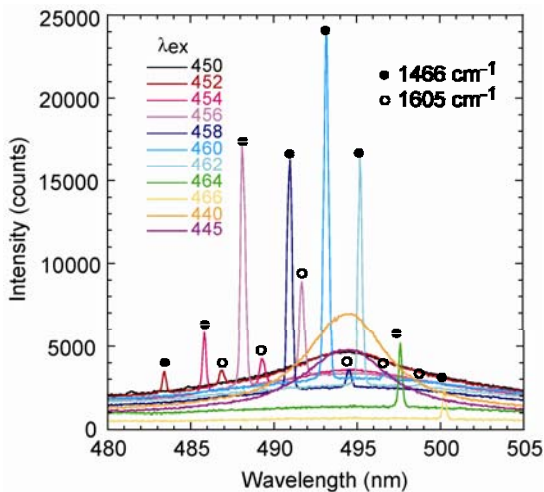


Photoluminescence spectra of BP1T crystal.

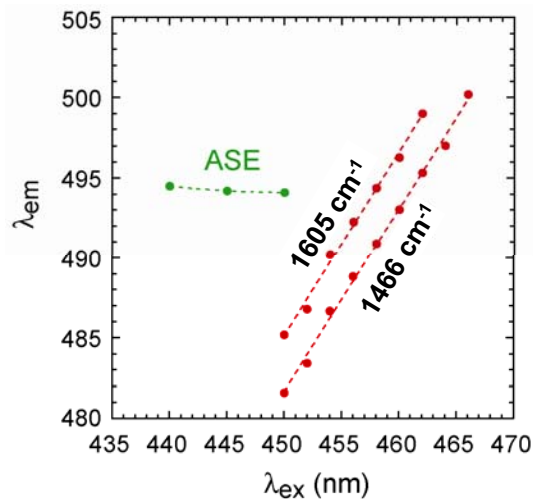


[H. Yanagi, A. Yoshiki, S. Hotta and S. Kobayashi, *Appl. Phys. Lett.* **83**, 1941 (2003)]

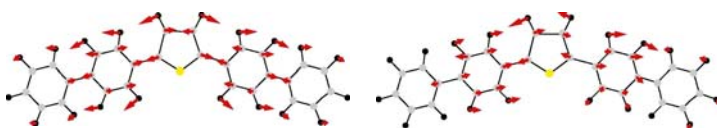
# BP1T結晶からの誘導共鳴ラマン散乱(SRRS)



PL spectra of BP1T crystal excited with YAG-OPO



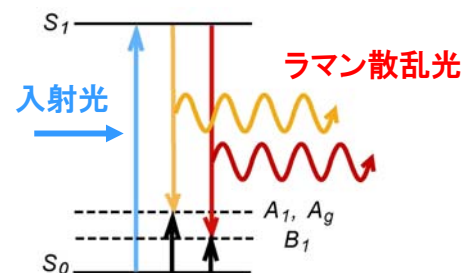
Changes in  $\lambda_{cm}$  as a function of  $\lambda_{ex}$ .



$A_1$  ( $1466\text{ cm}^{-1}$ )

$B_1$  ( $1605\text{ cm}^{-1}$ )

DFT-MO計算によるラマン活性な分子振動

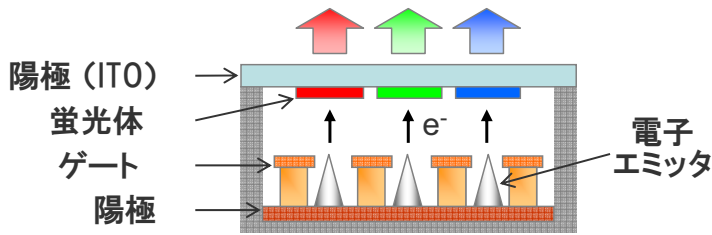


**Stimulated Resonance Raman Scattering (SRRS)**

微結晶、無共振器下、任意の波長で高利得

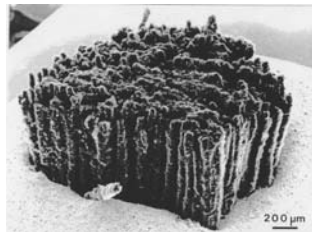
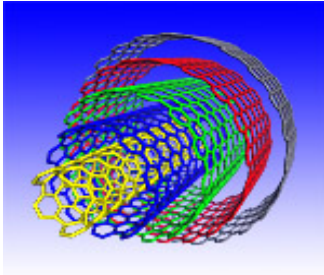
➡ 有機光増幅器、有機ラマンレーザー

# フィールドエミッションディスプレイ (FED)

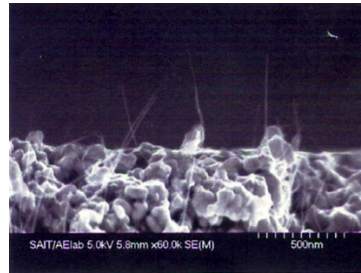


- Spindt-type metal (Mo) tip
- Anisotropic etching Si tip
- MIM, MIS tunnel junction
- Carbon nanotube (CNT) 高電流密度**
- III-V Nitrides 高安定性**

## CNT electron emitter



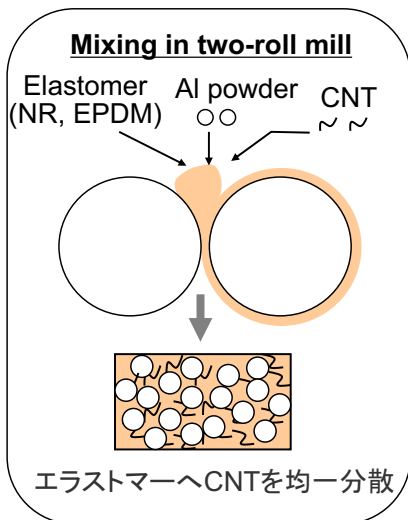
- Chemical Vapor Deposition
- Screen Printing
- CNT Composite



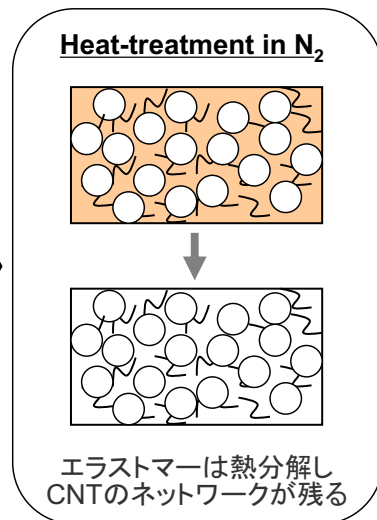
Samsung (1999)

# エラストマープリカーサー法(日信工業)によるCNT複合体の作製

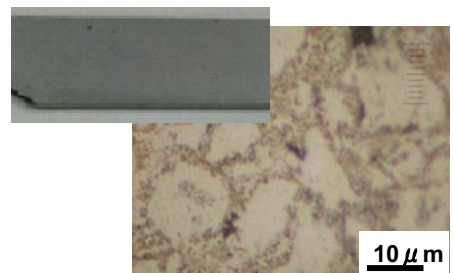
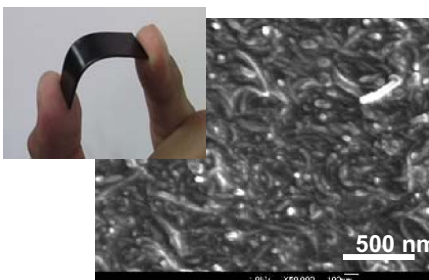
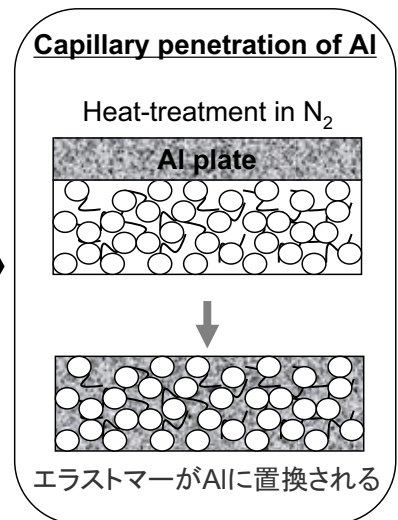
## 1. CNT/elastomer precursor

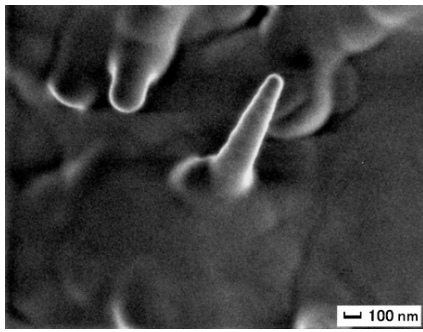


## 2. Removal of elastomer

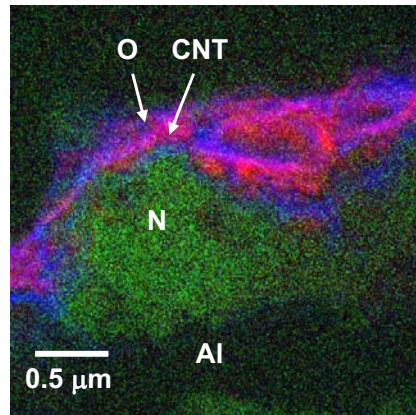


## 3. CNT/ metal composite

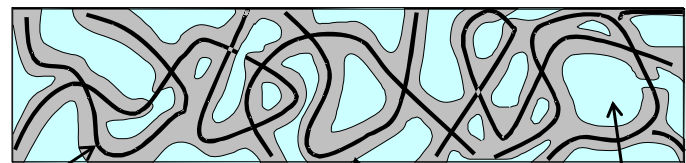
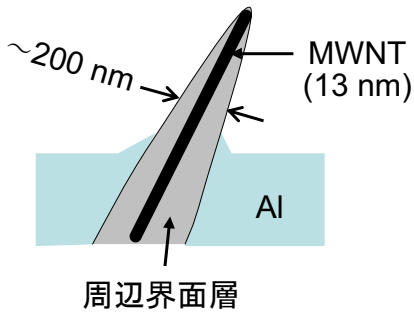




SEM image of CNT/Al composite



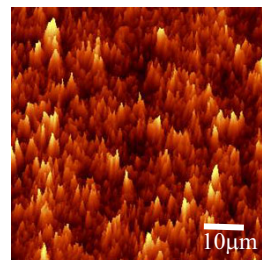
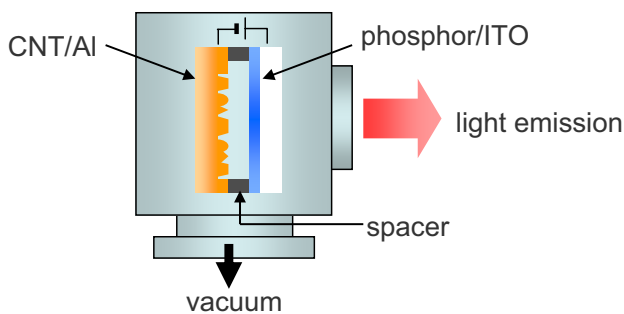
EELS mapping of CNT/Al composite



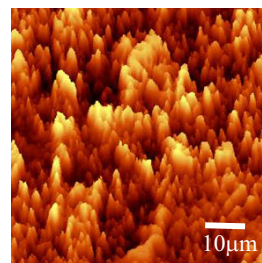
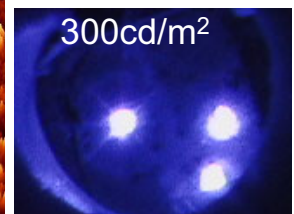
高電流密度  $\leftrightarrow$  AlN  
 有望な電子エミッタ  
 安定なIII-V 半導体電子エミッタ

[H. Yanagi, Y. Kawai, T. Kita, S. Fujii, Y. Hayashi, A. Magario and T. Noguchi. *Jpn. J. Appl. Phys.* **45**, L650 (2006)]

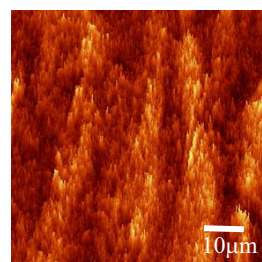
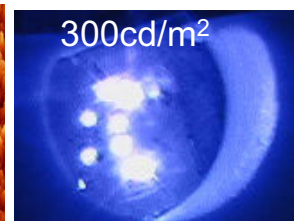
# CNT/Al複合体を用いたフィールドエミッションデバイス



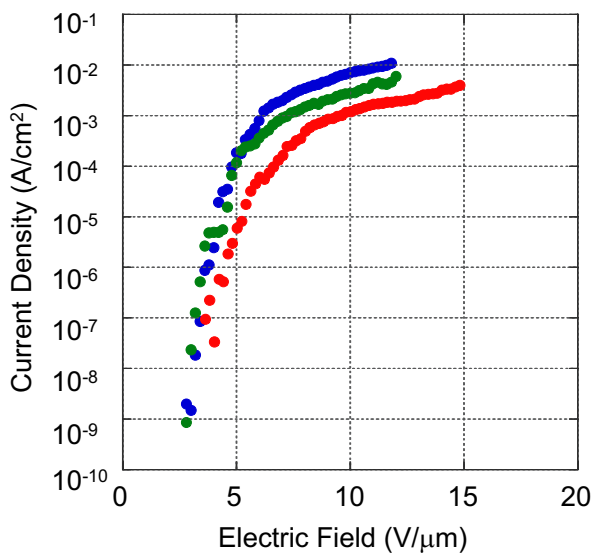
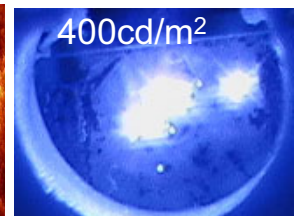
sand-paper rubbing



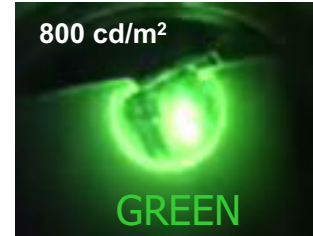
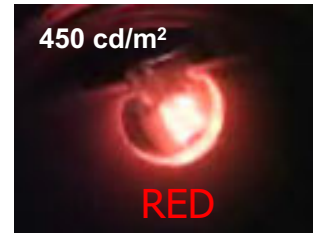
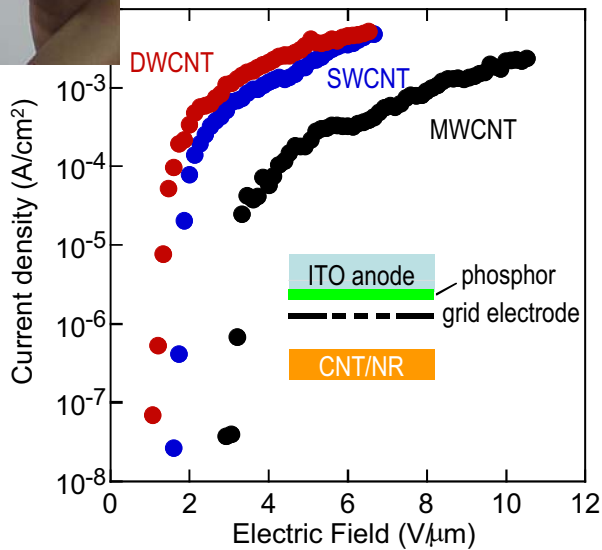
shot-blast with glass particles



polishing with diamond powder







フレキシブルFED

[T. Kita, Y. Hayashi, O. Wada, H. Yanagi, Y. Kawai, A. Magario, T. Noguchi. *Jpn. J. Appl. Phys.* **45**, L1186 (2006)]

## まとめ

### — ソフトマテリアルを用いた新しい発光デバイス —

#### ■ 1. 有機発光トランジスタ

電子トラップ抑制層と電子注入層の挿入により、低分子蒸着系有機トランジスタで両極性キャリア注入発光を実現した。

#### ■ 2. 有機発光増幅器と有機ラマンレーザー

$\pi$  共役オリゴマー結晶の誘導共鳴ラマン散乱(SRRS)現象に基づく高利得の無共振器レーザー作用を見出し、ポリマー薄膜を用いたプラスチックラマンレーザーへ応用展開した。

#### ■ 3. CNT複合体を用いたフィールドエミッションデバイス

CNT/エラストマー複合体シートを用いてITOレス化とフレキシブル化が可能な側面電子放出型フィールドエミッションデバイス(SEED)を開発した。